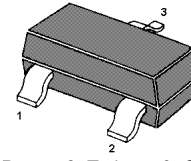


BCV26 / BCV46

PNP Darlington Transistors

for preamplifier input applications



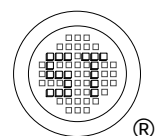
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

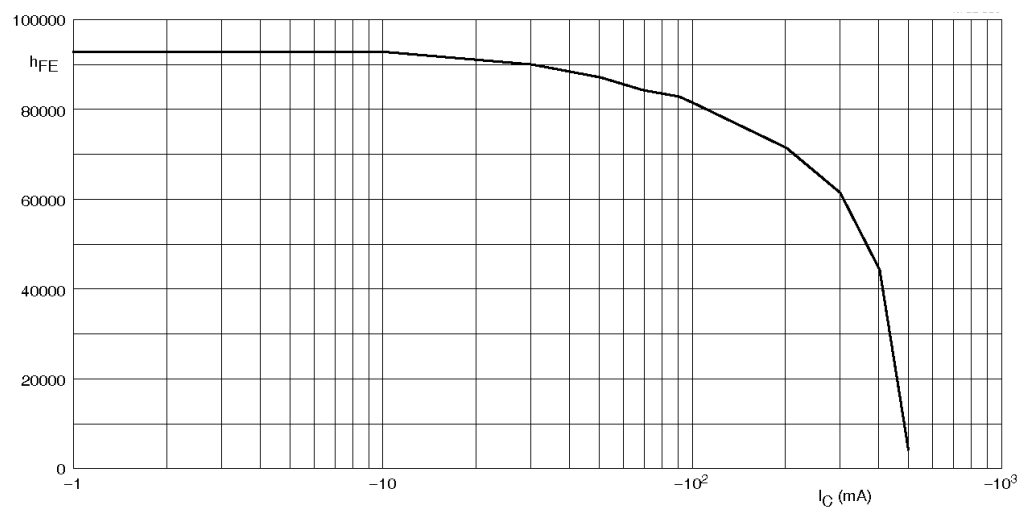
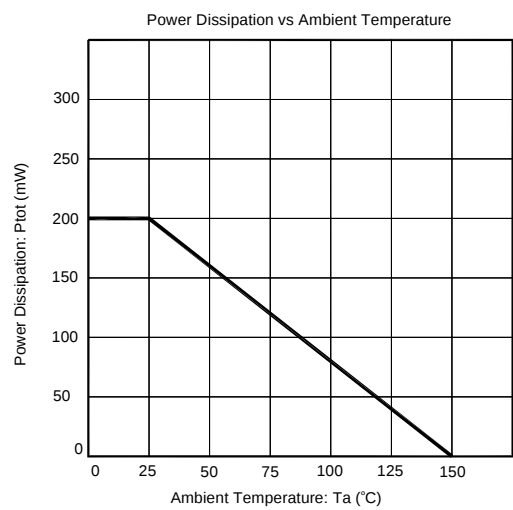
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	BCV26 BCV46 $-V_{CBO}$	40 80	V
Collector Emitter Voltage	BCV26 BCV46 $-V_{CEO}$	30 60	V
Emitter Base Voltage	$-V_{EBO}$	10	V
Collector Current	$-I_C$	500	mA
Peak Collector Current	$-I_{CM}$	800	mA
Base Current	$-I_B$	100	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$	BCV26 BCV46 h_{FE}	4000 2000	- -	- -	-
at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	BCV26 BCV46 h_{FE}	10000 4000	- -	- -	-
at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$	BCV26 BCV46 h_{FE}	20000 10000	- -	- -	-
Collector Base Cutoff Current					
at $-V_{CB} = 30\text{ V}$	BCV26 $-I_{CBO}$	-	-	100	nA
at $-V_{CB} = 60\text{ V}$	BCV46 $-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage	BCV26 BCV46 $-V_{(BR)CBO}$	40 80	- -	- -	V
Collector Emitter Breakdown Voltage	BCV26 BCV46 $-V_{(BR)CEO}$	30 60	- -	- -	V
Emitter Base Breakdown Voltage	$-V_{(BR)EBO}$	10	-	-	V
Collector Emitter Saturation Voltage	$-V_{CE(sat)}$	-	-	1	V
Base Emitter Saturation Voltage	$-V_{BE(sat)}$	-	-	1.5	V
Base Emitter On-state Voltage	$-V_{BE(on)}$	-	-	1.4	V
Transition Frequency	f_T	-	220	-	MHz
at $-V_{CE} = 5\text{ V}$, $-I_C = 30\text{ mA}$, $f = 100\text{ MHz}$					





$V_{CE} = -2\text{ V}$.

DC current gain; typical values.

